

MODULE CONFIGURATIONS

Viking Part Number	Capacity	Module Configuration	Device Configuration	Device Package	Module Ranks	Performance	CAS Latency
VR7WU287298FBZ	1GB	128Mx72	128Mx8	FBGA	1	PC3-6400	CL6 (6-6-6)
VR7WU287298FBA	1GB	128Mx72	128Mx8	FBGA	1	PC3-8500	CL7 (7-7-7)
VR7WU287298FBD	1GB	128Mx72	128Mx8	FBGA	1	PC3-10600	CL9 (9-9-9)
VR7WU287298FBF	1GB	128Mx72	128Mx8	FBGA	1	PC3-12800	CL11 (11-11-11)
VR7WU567298GBZ	2GB	256Mx72	256Mx8	FBGA	1	PC3-6400	CL6 (6-6-6)
VR7WU567298GBA	2GB	256Mx72	256Mx8	FBGA	1	PC3-8500	CL7 (7-7-7)
VR7WU567298GBD	2GB	256Mx72	256Mx8	FBGA	1	PC3-10600	CL9 (9-9-9)
VR7WU567298GBF	2GB	256Mx72	256Mx8	FBGA	1	PC3-12800	CL11 (11-11-11)
VR7WU127298HBZ	4GB	512Mx72	512Mx8	FBGA	1	PC3-6400	CL6 (6-6-6)
VR7WU127298HBA	4GB	512Mx72	512Mx8	FBGA	1	PC3-8500	CL7 (7-7-7)
VR7WU127298HBD	4GB	512Mx72	512Mx8	FBGA	1	PC3-10600	CL9 (9-9-9)
VR7WU127298HBF	4GB	512Mx72	512Mx8	FBGA	1	PC3-12800	CL11 (11-11-11)
VR7WU127298GHZ	4GB	512Mx72	256Mx8	BGA stack	2	PC3-6400	CL6 (6-6-6)
VR7WU127298GHA	4GB	512Mx72	256Mx8	BGA stack	2	PC3-8500	CL7 (7-7-7)
VR7WU127298GHD	4GB	512Mx72	256Mx8	BGA stack	2	PC3-10600	CL9 (9-9-9)
VR7WU127298GHF	4GB	512Mx72	256Mx8	BGA stack	2	PC3-12800	CL11 (11-11-11)
VR7WU1G7298HHZ	8GB	1Gx72	512Mx8	BGA stack	2	PC3-6400	CL6 (6-6-6)
VR7WU1G7298HHA	8GB	1Gx72	512Mx8	BGA stack	2	PC3-8500	CL7 (7-7-7)
VR7WU1G7298HHD	8GB	1Gx72	512Mx8	BGA stack	2	PC3-10600	CL9 (9-9-9)
VR7WU1G7298HHF	8GB	1Gx72	512Mx8	BGA stack	2	PC3-12800	CL11 (11-11-11)

Note: For part numbers containing an x, contact Viking for the complete PN

Features

- JEDEC standard Power Supply
 - VDD = VDDQ = 1.35V (1.283V to 1.45V)
 - VDDSPD = +3.0V to +3.6V
 - Backward Compatible with 1.5V DDR3 DIMMs
 - VDD = 1.5V (1.425V to 1.575V)
- 244pin Very Low Profile Mini Unbuffered Dual-In-Line Memory Module.
- 8 Internal Banks.
- Programmable CAS Latency: 6, 7, 8, 9, 10, 11
- Programmable CAS Write Latency (CWL).
- Programmable Additive Latency (Posted CAS).
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Selectable BC4 or BL8 on-the-fly (OTF)
- On-Die-Termination (ODT) and Dynamic ODT for improved signal integrity.
- Refresh, Self Refresh and Power Down Modes.
- Serial Presence Detect with EEPROM.
- On-DIMM Thermal Sensor.
- RoHS Compliant* (see last page)

Nomenclature

Module Standard	SDRAM Standard	Clock
PC3-6400	DDR3-800	400MHz
PC3-8500	DDR3-1066	533MHz
PC3-10600	DDR3-1333	667MHz
PC3-12800	DDR3-1600	800MHz

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PIN CONFIGURATIONS

Pin	Front Side	Pin	Back Side	Pin	Front Side	Pin	Back Side	Pin	Front Side	Pin	Back Side	Pin	Front Side	Pin	Back Side
1	VTT, NC	123	VTT, NC	32	DQ25	154	VSS	63	VDD	185	VDD	92	DQ40	214	DQ45
2	VREFDQ	124	VSS	33	VSS	155	DM3,DQS12, TDQS12	64	NC, CK1	186	CK0	93	DQ41	215	VSS
3	VSS	125	DQ4	34	DQS3#	156	NC,DQS12#, TDQS12#	65	NC, CK1#	187	CK0#	94	VSS	216	DM5,DQS14, TDQS14
4	DQ0	126	DQ5	35	DQS3	157	VSS	KEY				95	DQS5#	217	NC, DQS14#, TDQS14#
5	DQ1	127	VSS	36	VSS	158	DQ30					96	DQS5	218	VSS
6	VSS	128	DM0,DQS9, TDQS9	37	DQ26	159	DQ31	66	VDD	188	VDD	97	VSS	219	DQ46
7	DQS0#	129	NC,DQS9#, TDQS9#	38	DQ27	160	VSS	67	VREFCA	189	VDD	98	DQ42	220	DQ47
8	DQS0	130	VSS	39	VSS	161	CB4	68	VDD	190	EVENT#	99	DQ43	221	VSS
9	VSS	131	DQ6	40	CB0	162	CB5	69	NC	191	A0	100	VSS	222	DQ52
10	DQ2	132	DQ7	41	CB1	163	VSS	70	VDD	192	VDD	101	DQ48	223	DQ53
11	DQ3	133	VSS	42	VSS	164	DM8,DQS17, TDQS17	71	A10 / AP	193	BA1	102	DQ49	224	VSS
12	VSS	134	DQ12	43	DQS8#	165	NC,DQS17#, TDQS17#	72	BA0	194	VDD	103	VSS	225	DM6,DQS15, TDQS15
13	DQ8	135	DQ13	44	DQS8	166	VSS	73	VDD	195	RAS#	104	DQS6#	226	NC,DQS15#, TDQS15#
14	DQ9	136	VSS	45	VSS	167	CB6	74	WE#	196	S0#	105	DQS6	227	VSS
15	VSS	137	DM1,DQS10, TDQS10	46	CB2	168	CB7	75	CAS#	197	VDD	106	VSS	228	DQ54
16	DQS1#	138	NC,DQS10#, TDQS10#	47	CB3	169	VSS	76	VDD	198	ODT0	107	DQ50	229	DQ55
17	DQS1	139	VSS	48	VSS	170	RFU	77	S1#, NC	199	A13	108	DQ51	230	VSS
18	VSS	140	DQ14	49	RFU	171	NC(TEST)	78	ODT1, NC	200	VDD	109	VSS	231	DQ60
19	DQ10	141	DQ15	50	RESET#	172	CKE1, NC	79	VDD	201	S3#, NC	110	DQ56	232	DQ61
20	DQ11	142	VSS	51	CKE0	173	VDD	80	S2#, NC	202	RFU	111	DQ57	233	VSS
21	VSS	143	DQ20	52	VDD	174	A15, NC	81	RFU	203	VSS	112	VSS	234	DM7,DQS16, TDQS16
22	DQ16	144	DQ21	53	BA2	175	A14	82	VSS	204	DQ36	113	DQS7#	235	NC,DQS16#, TDQS16#
23	DQ17	145	VSS	54	NC	176	VDD	83	DQ32	205	DQ37	114	DQS7	236	VSS
24	VSS	146	DM2,DQS11, TDQS11	55	VDD	177	A12 / BC#	84	DQ33	206	VSS	115	VSS	237	DQ62
25	DQS2#	147	NC,DQS11#, TDQS11#	56	A11	178	A9	85	VSS	207	DM4,DQS13, TDQS13	116	DQ58	238	DQ63
26	DQS2	148	VSS	57	A7	179	VDD	86	DQS4#	208	NC,DQS13#, TDQS13#	117	DQ59	239	VSS
27	VSS	149	DQ22	58	VDD	180	A8	87	DQS4	209	VSS	118	VSS	240	VDDSPD
28	DQ18	150	DQ23	59	A5	181	A6	88	VSS	210	DQ38	119	SA0	241	SA1
29	DQ19	151	VSS	60	A4	182	VDD	89	DQ34	211	DQ39	120	SCL	242	SDA
30	VSS	152	DQ28	61	VDD	183	A3	90	DQ35	212	VSS	121	SA2	243	VSS
31	DQ24	153	DQ29	62	A2	184	A1	91	VSS	213	DQ44	122	VTT	244	VTT

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PIN FUNCTION DESCRIPTION

SYMBOL	TYPE	POLARITY	DESCRIPTION
CK0	IN	Positive Edge	Positive line of the differential pair of system clock inputs.
CK0#	IN	Negative Edge	Negative line of the differential pair of system clock inputs.
CKE[1:0]	IN	Active High	CKE HIGH activates, and CKE LOW deactivates internal clock signals, and device input buffers and output drivers of the SDRAMs. Taking CKE LOW provides PRECHARGE POWER-DOWN and SELF REFRESH operation (all banks idle), or ACTIVE POWER DOWN (row ACTIVE in any bank)
S[3:0]#	IN	Active Low	Enables the associated SDRAM command decoder when low and disables decoder when high. When decoder is disabled, new commands are ignored and previous operations continue. These input signals also disable all outputs (except CKE and ODT) of the register(s) on the DIMM when both inputs are high. When both S[1:0] are high, all register outputs (except CKE, ODT and Chip select) remain in the previous state. For modules supporting 4 ranks, S[3:2] operate similarly to S[1:0] for a second set of register outputs.
ODT[1:0]	IN	Active High	On-Die Termination control signals
RAS#, CAS#, WE#	IN	Active Low	When sampled at the positive rising edge of the clock, CAS#, RAS#, and WE# define the operation to be executed by the SDRAM.
VREFDQ	Supply		Reference voltage for DQ0-DQ63 and CB0-CB7.
VREFCA	Supply		Reference voltage for A0-A15, BA0-BA2, RAS#, CAS#, WE#, S0#, S1#, CKE0, CKE1, Par_In, ODT0 and ODT1.
BA[2:0]	IN	-	Selects which SDRAM bank of eight is activated. BA0 - BA2 define to which bank an Active, Read, Write or Precharge command is being applied. Bank address also determines mode register is to be accessed during an MRS cycle.
A[15:13, 12/BC, 11, 10/AP, 9:0]	IN	-	Provided the row address for Active commands and the column address and Auto Precharge bit for Read/Write commands to select one location out of the memory array in the respective bank. A10 is sampled during a Precharge command to determine whether the Precharge applies to one bank (A10 LOW) or all banks (A10 HIGH). If only one bank is to be precharged, the bank is selected by BA. A12 is also utilized for BL 4/8 identification for "BL on the fly" during CAS# command. The address inputs also provide the op-code during Mode Register Set commands.
DQ [63:0], CB [7:0]	I/O	-	Data and Check Bit Input/Output pins
VDD, VSS	Supply	-	Power and ground for the DDR SDRAM input buffers and core logic.
DM [8:0]	IN	Active High	Masks write data when high, issued concurrently with input data.
VDD, VSS	Supply		Power and ground for the DDR SDRAM input buffers and core logic.
VTT	Supply		Termination Voltage for Address/Command/Control/Clock nets.
DQS[17:0]	I/O	Positive Edge	Positive line of the differential data strobe for input and output data.
DQS [17:0]#	I/O	Negative Edge	Negative line of the differential data strobe for input and output data.
TDQS[17:9], TDQS[17:9]#	OUT		TDQS, TDQS# is applicable for X8 DRAMs only. When enabled via Mode Register A11=1 in MR1, DRAM will enable the same termination resistance function on TDQS, TDQS# that is applied to DQS, DQS#. When disabled via mode register A11=0 in MR1, DM, TDQS will provide the data mask function and TDQS# is not used. X4/X16 DRAMs must disable the TDQS function via mode register A11=0 in MR1
SA [2:0]	IN	-	These signals are tied at the system planar to either VSS or VDDSPD to configure the serial SPD EEPROM address range.
SDA	I/O	-	This bidirectional pin is used to transfer data into or out of the SPD EEPROM. A resistor must be connected from the SDA bus line to VDDSPD on the system planar to act as a pull-up.
SCL	IN	-	This signal is used to clock data into and out of the SPD EEPROM. A resistor may be connected from the SCL bus line to VDDSPD on the system planar to act as a pull-up.
EVENT#	OUT (open drain)	Active Low	This signal indicates that a thermal event has been detected in the thermal sensing device. The system should guarantee the electrical level requirement is met for the EVENT pin on TS/SPD part.

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PIN FUNCTION DESCRIPTION

SYMBOL	TYPE	POLARITY	DESCRIPTION
RESET#	IN		The RESET# pin is connected to the RESET# pin on each DRAM. When low, all DRAMs are set to a known state.
VDDSPD	Supply	-	Serial EEPROM positive power supply wired to a separate power pin at the connector which supports from 3.0 Volt to 3.6 Volt (nominal 3.3V) operation.
TEST			Used by memory bus analysis tools (unused (NC) on memory DIMMs)

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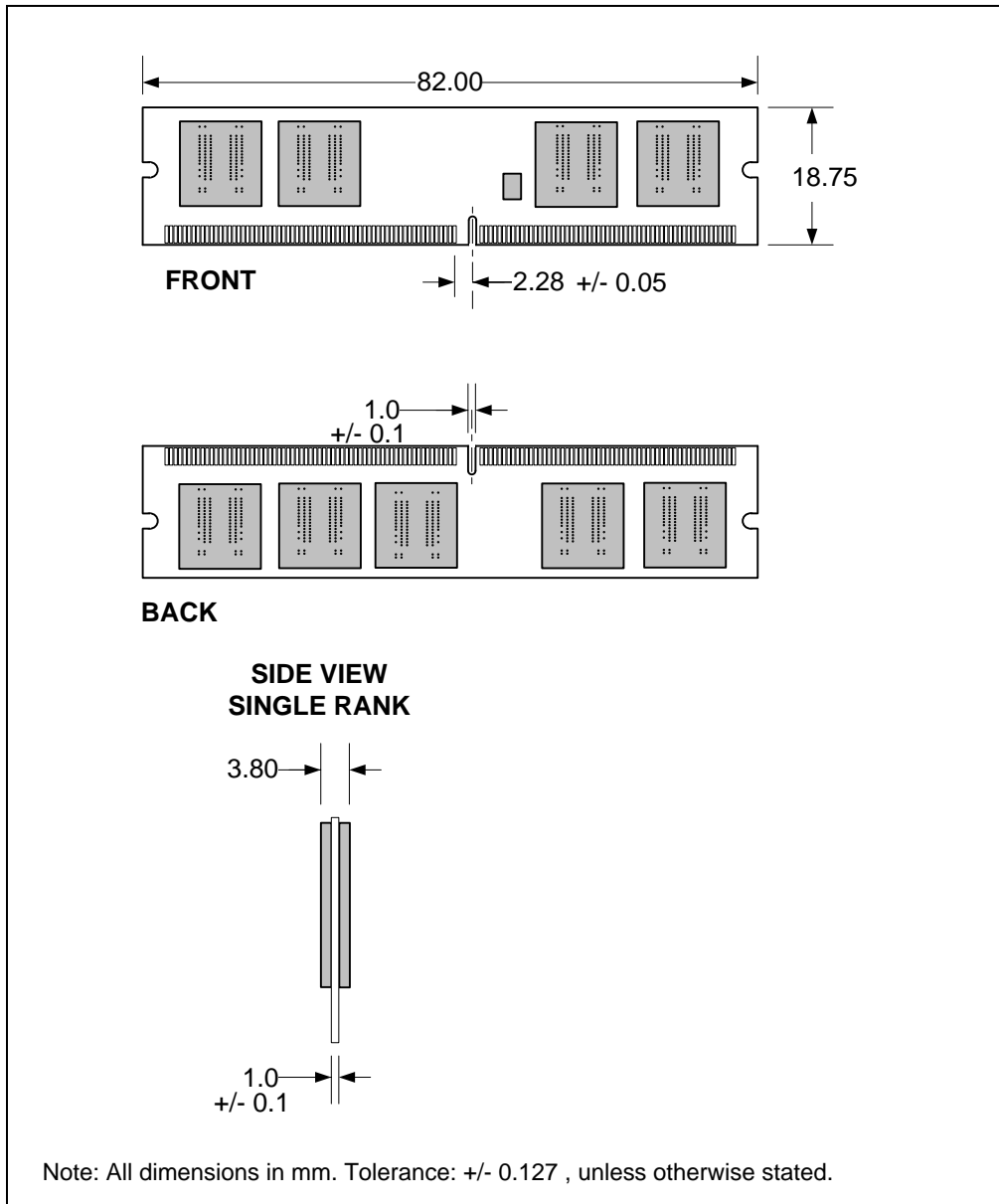
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MECHANICAL OUTLINE

Single Rank Outline



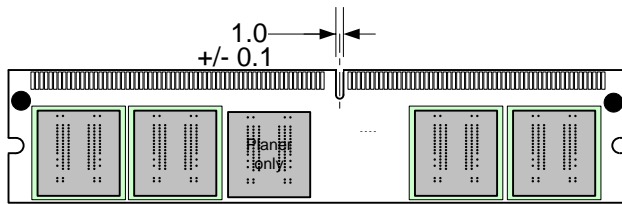
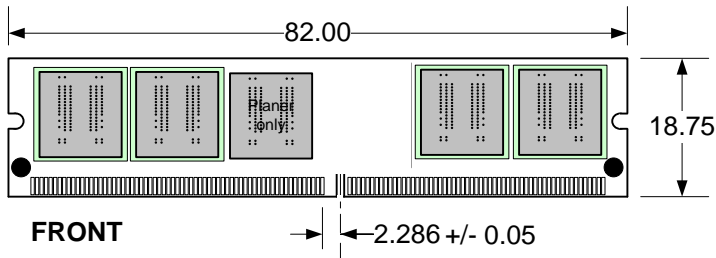
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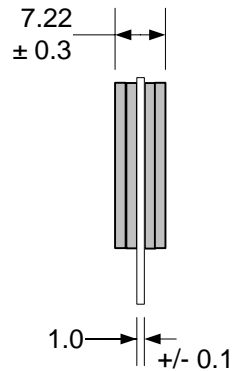
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Dual Rank Outline



SIDE VIEW DUAL RANK BGA-Stack



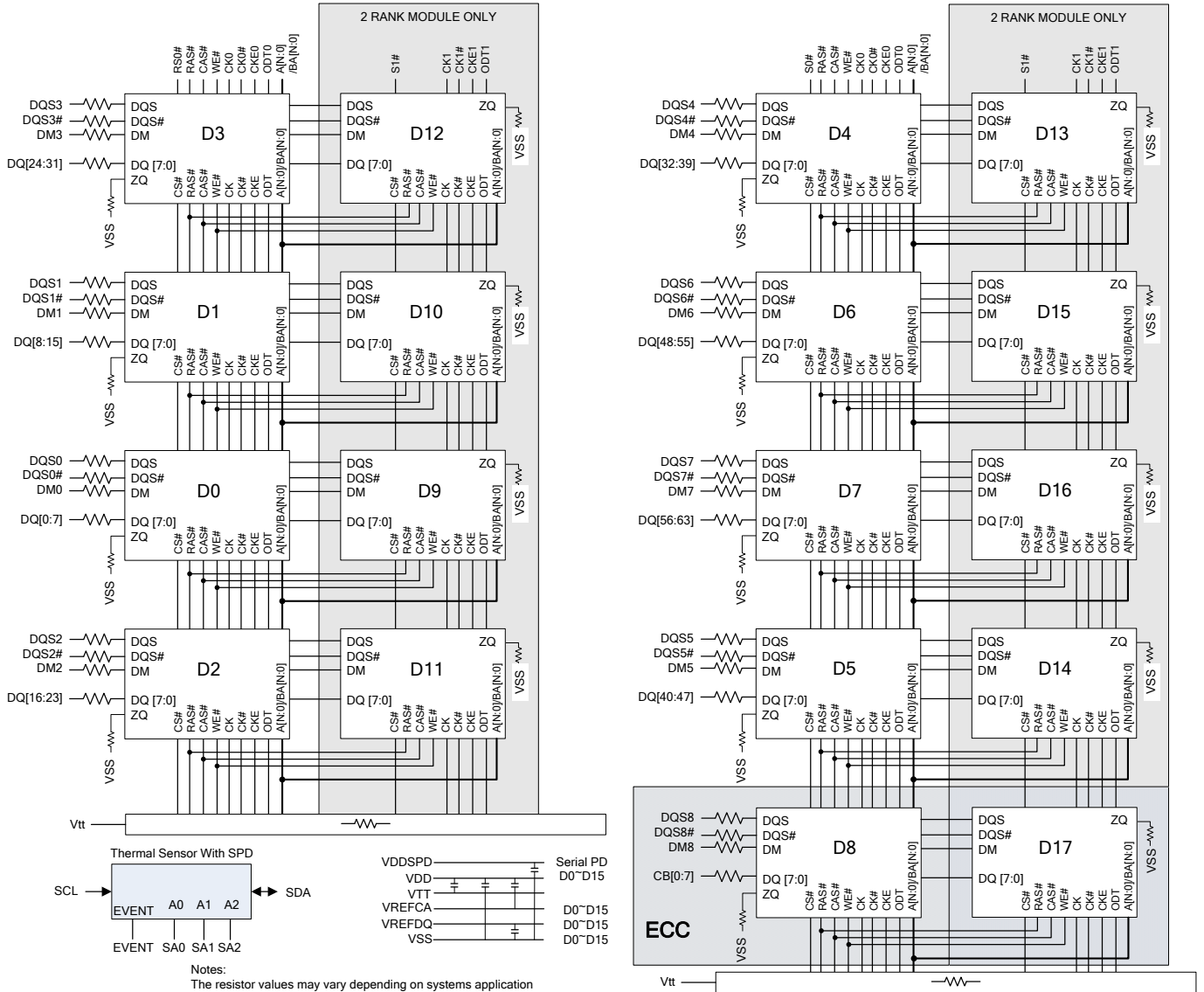
Note: 1) All dimensions in mm. Tolerance: +/- 0.127mm , unless otherwise stated.
2) All placements can be BGA-stacked or planer, unless otherwise stated

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FUNCTIONAL BLOCK DIAGRAM



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ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Voltage on any pin relative to GND	Vin, Vout	-0.4 ~ 1.975	V
Voltage on VDD supply relative to GND	VDD	-0.4 ~ 1.975	V
Voltage on VDDQ supply relative to GND	VDDQ	-0.4 ~ 1.975	V
Storage temperature	TSTG	-55 ~ +100	°C

Note: Permanent device damage may occur if 'ABSOLUTE MAXIMUM RATINGS' are exceeded. Functional operation should be restricted to recommended operating condition. Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

DC OPERATING CONDITIONS AND CHARACTERISTICS (SSTL_1.35)

Recommended operating conditions (Voltages referenced to GND, Tcase = 0 to 85°C)

Parameter	Symbol	Min.	Max.	Unit	Notes
Case Temperature	Tcase	0	95	°C	5
Supply voltage @ 1.35V	VDD	1.283	1.45	V	1, 2
Supply voltage for DQ, DQS @ 1.35V	VDDQ	1.283	1.45	V	1, 2
Supply voltage @ 1.5V	VDD	1.425	1.575	V	1, 2
Supply voltage for DQ, DQS @ 1.5V	VDDQ	1.425	1.575	V	1, 2
Reference Voltage for DQ, DM inputs	VREFDQ(DC)	0.49 x VDD	0.51 x VDD	V	3, 4
Reference Voltage for ADD, CMD inputs	VREFCA(DC)	0.49 x VDD	0.51 x VDD	V	3, 4
Terminal Voltage	VTT	0.49 x VDD	0.51 x VDD	V	3, 4
EEPROM Supply Voltage	VDDSPD	1.7	3.6	V	
Input high voltage	VIH(AC)	VREF + 0.175	-	V	
	VIH(DC)	VREF + 0.100	VDD		
Input low voltage	VIL(AC)	-	VREF - 0.175	V	
	VIL(DC)	VSS	VREF - 0.100		
Input leakage current	Single Rank	IIL	-18	18	µA
Output leakage current	Single Rank	IOL	-5	5	µA
Input leakage current	Dual Rank	IIL	-36	36	µA
Output leakage current	Dual Rank	IOL	-10	10	µA

- Note:**
1. VDDQ tracks with VDD. AC parameters are measured with VDD and VDDQ tied together
 2. Under all conditions VDDQ must be less than or equal to VDD.
 3. The ac peak noise on VREF may not allow VREF to deviate from VREF.DC by more than ±1% VDD (for reference: approx. ± 15 mV).
 4. For reference: approx. VDD/2 ± 15 mV.
 5. Refresh rate required to be doubled (tREFI = 3.9µs) when 85°C < TC < 95°C.

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DEVICE CAPACITANCE

Parameter	Symbol	DDR3-800		DDR3-1066		DDR3-1333		Units	Notes
		Min	Max	Min	Max	Min	Max		
Input/output capacitance (DQ, DM, DQS, DQS#, TDQS,TDQS#)	CIO	1.5	3.0	1.5	2.7	1.5	2.5	pF	1,2,3
Input capacitance, CK and CK#	CCK	0.8	1.6	0.8	1.6	0.8	1.4	pF	2,3
Input capacitance delta, CK and CK#	CDCK	0	0.15	0	0.15	0	0.15	pF	2,3,4
Input/output capacitance delta DQS and DQS#	CDDQS	0	0.2	0	0.2	0	0.15	pF	2,3,5
Input capacitance, (CTRL, ADD, CMD input-only pins)	CI	0.75	1.4	0.75	1.35	0.75	1.3	pF	2,3,6
Input/output capacitance of ZQ pin	CZQ	-	3	-	3	-	3	pF	2,3,7

DEVICE CAPACITANCE (Cont.)

Parameter	Symbol	DDR3-1600		DDR3-1866		Min	Max	Units	Notes
		Min	Max	Min	Max				
Input/output capacitance (DQ, DM, DQS, DQS#, TDQS,TDQS#)	CIO	1.5	2.3	1.4	2.2			pF	1,2,3
Input capacitance, CK and CK#	CCK	0.8	1.4	0.8	1.3			pF	2,3
Input capacitance delta, CK and CK#	CDCK	0	0.15	0	0.15			pF	2,3,4
Input/output capacitance delta DQS and DQS#	CDDQS	0	0.15	0	0.15			pF	2,3,5
Input capacitance, (CTRL, ADD, CMD input-only pins)	CI	0.75	1.3	0.75	1.2			pF	2,3,6
Input/output capacitance of ZQ pin	CZQ	-	3	-	3			pF	2,3,7

Note:

1. Although the DM, TDQS and TDQS# pins have different functions, the loading matches DQ and DQS
2. This parameter is not subject to production test. It is verified by design and characterization. The capacitance is measured according to JEP147 ("PROCEDURE FOR MEASURING INPUT CAPACITANCE USING A VECTOR NETWORK ANALYZER(VNA)") with VDD, VDDQ, VSS, VSSQ applied and all other pins floating (except the pin under test, CKE, RESET# and ODT as necessary). VDD=VDDQ=1.35V, VBIAS=VDD/2 and on die termination off.
3. This parameter applies to monolithic devices only; stacked/dual-die devices are not covered here
4. Absolute value of CCK-CCK#
5. Absolute value of CIO(DQS)-CIO(DQS#)
6. CI applies to ODT, CS#, CKE, A0-A15, BA0-BA2, RAS#, CAS#, WE#.
7. Maximum external load capacitance on ZQ pin: 5 pF.

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DC CHARACTERISTICS DEFINITIONS (Recommended operating conditions unless otherwise noted, Tcase = 0 to 85 °C)

Symbol	Conditions	Units	Notes
IDD0	Operating one bank active-precharge current; tCK = tCK(IDD), tRC = tRC(IDD), tRAS = tRASmin(IDD); CKE is HIGH, CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	1, 2
IDD1	Operating one bank active-read-precharge current; IOUT = 0mA; BL = 8, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRC = tRC(IDD), tRAS = tRASmin(IDD), tRCD = tRCD(IDD); CKE is HIGH, CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W	mA	1, 2
IDD2P-S	Precharge power-down current (slow exit); All banks idle; tCK = tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	mA	1, 3
IDD2P-F	Precharge power-down current (fast exit); All banks idle; tCK = tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	mA	1, 3
IDD2Q	Precharge quiet standby current; All banks idle; tCK = tCK(IDD); CKE is HIGH, CS is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	mA	1, 3
IDD2N	Precharge standby current; All banks idle; tCK = tCK(IDD); CKE is HIGH, CS is HIGH; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	1, 3
IDD3P	Active power-down current; All banks open; tCK = tCK(IDD); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	mA	1, 3
IDD3N	Active standby current; All banks open; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, CS is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	1, 3
IDD4W	Operating burst write current; All banks open, Continuous burst writes; BL = 8, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	1, 2
IDD4R	Operating burst read current; All banks open, Continuous burst reads, IOUT = 0mA; BL = 8, CL = CL(IDD), AL = 0; tCK = tCK(IDD), tRAS = tRASmax(IDD), tRP = tRP(IDD); CKE is HIGH, CS is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as IDD4W	mA	1, 2
IDD5B	Burst refresh current; tCK = tCK(IDD); Refresh command at every tRFC(IDD) interval; CKE is HIGH, CS is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	mA	1, 3
IDD6	Self refresh current; CK and CK at 0V; CKE ≤ 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING	mA	1, 3
IDD6ET	Extended Temperature Range Self-Refresh Current; CK and CK at 0V; CKE ≤ 0.2V; Other control and address inputs are FLOATING; Data Bus inputs are FLOATING, PASR disabled, Applicable for MR2 setting A6=0 and A7=1	mA	1, 3
IDD7	Operating bank interleave read current; All bank interleaving reads, IOUT = 0mA; BL = 8, CL = CL(IDD), AL = tRCD(IDD)-1*tCK(IDD); tCK = tCK(IDD), tRC = tRC(IDD), tRRD = tRRD(IDD), tRCD = 1*tCK(IDD); CKE is HIGH, CS is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data pattern is same as IDD4R;	mA	1, 2

Notes:

1. Calculated values are from component data.
2. One module rank in the active IDD; the other rank in IDD2P-S (slow exit)
3. All ranks in this IDD condition.

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DC CHARACTERISTICS CURRENTS SINGLE RANK 1Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0	720	828	900	954	982	mA
IDD1	900	1035	1125	1188	1233	mA
IDD2P-S	72	72	72	75	75	mA
IDD2P-F	234	252	270	281	321	mA
IDD2Q	495	585	675	694	734	mA
IDD2N	495	585	675	694	732	mA
IDD3P	270	360	405	419	442	mA
IDD3N	585	675	765	777	807	mA
IDD4R	1260	1530	1890	2086	2252	mA
IDD4W	1440	1800	2070	2314	2499	mA
IDD5B	1710	1800	1890	1916	1955	mA
IDD6	90	90	90	90	90	mA
IDD6ET	108	108	108	108	123	mA
IDD7	1890	2250	2700	2768	2913	mA

DC CHARACTERISTICS CURRENTS DUAL RANK 1Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0	1037	1192	1296	1374	1414	mA
IDD1	1296	1491	1620	1711	1776	mA
IDD2P-S	103	103	103	108	108	mA
IDD2P-F	337	363	388	404	462	mA
IDD2Q	713	842	972	999	1057	mA
IDD2N	713	842	972	999	1054	mA
IDD3P	388	518	583	603	636	mA
IDD3N	842	972	1102	1119	1162	mA
IDD4R	1815	2204	2722	3005	3244	mA
IDD4W	2074	2593	2982	3333	3600	mA
IDD5B	2463	2593	2722	2760	2816	mA
IDD6	129	129	129	129	129	mA
IDD6ET	155	155	155	155	177	mA
IDD7	2722	3241	3889	3987	4196	mA

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DC CHARACTERISTICS CURRENTS SINGLE RANK 2Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0	819	945	1053	1117	1150	mA
IDD1	1008	1125	1224	1293	1342	mA
IDD2P-S	117	117	117	122	122	mA
IDD2P-F	225	297	315	328	374	mA
IDD2Q	648	594	675	694	734	mA
IDD2N	477	603	693	713	752	mA
IDD3P	288	378	423	438	462	mA
IDD3N	513	648	747	759	788	mA
IDD4R	1413	1755	2070	2285	2467	mA
IDD4W	1161	1485	1755	1961	2117	mA
IDD5B	2322	2439	2529	2564	2616	mA
IDD6	108	108	108	108	108	mA
IDD6ET	108	108	108	108	123	mA
IDD7	2403	2646	3213	3293	3466	mA

DC CHARACTERISTICS CURRENTS DUAL RANK 2Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0	1179	1361	1516	1609	1656	mA
IDD1	1452	1620	1763	1862	1933	mA
IDD2P-S	168	168	168	175	175	mA
IDD2P-F	324	427	453	472	538	mA
IDD2Q	933	855	972	999	1057	mA
IDD2N	687	868	998	1027	1083	mA
IDD3P	414	544	609	630	665	mA
IDD3N	739	933	1076	1093	1135	mA
IDD4R	2035	2528	2982	3291	3553	mA
IDD4W	1672	2139	2528	2825	3049	mA
IDD5B	3345	3513	3643	3693	3768	mA
IDD6	155	155	155	155	155	mA
IDD6ET	155	155	155	155	177	mA
IDD7	3461	3811	4628	4743	4993	mA

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DC CHARACTERISTICS CURRENTS SINGLE RANK 4Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0	495	396	423	495	558	mA
IDD1	595	531	558	594	630	mA
IDD2P-S	180	162	162	162	162	mA
IDD2P-F	252	234	252	288	333	mA
IDD2Q	324	243	252	288	315	mA
IDD2N	351	252	261	288	315	mA
IDD3P	400	288	315	342	369	mA
IDD3N	378	288	315	342	369	mA
IDD4R	1035	1107	1260	1413	1566	mA
IDD4W	855	855	990	1125	1269	mA
IDD5B	1800	2016	2052	2115	2178	mA
IDD6	198	180	180	180	180	mA
IDD6ET	252	225	225	225	225	mA
IDD7	1530	1440	1710	1980	2259	mA

DC CHARACTERISTICS CURRENTS DUAL RANK 4Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0	713	558	585	657	720	mA
IDD1	842	693	720	756	792	mA
IDD2P-S	259	324	324	324	324	mA
IDD2P-F	363	468	504	576	666	mA
IDD2Q	466	486	504	576	630	mA
IDD2N	505	504	522	576	630	mA
IDD3P	583	576	630	684	738	mA
IDD3N	544	576	630	684	738	mA
IDD4R	1491	1269	1422	1575	1728	mA
IDD4W	1231	1017	1152	1287	1431	mA
IDD5B	2593	2016	2052	2115	2178	mA
IDD6	285	360	360	360	360	mA
IDD6ET	363	450	450	450	450	mA
IDD7	2204	1602	1872	2142	2421	mA

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DC CHARACTERISTICS CURRENTS SINGLE RANK 8Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0				603	621	mA
IDD1				702	729	mA
IDD2P-S				99	99	mA
IDD2P-F				126	144	mA
IDD2Q				306	324	mA
IDD2N				324	342	mA
IDD3P				324	342	mA
IDD3N				459	477	mA
IDD4R				1125	1215	mA
IDD4W				1125	1215	mA
IDD5B				2205	2250	mA
IDD6				216	216	mA
IDD6ET				306	306	mA
IDD7				1710	1800	mA

DC CHARACTERISTICS CURRENTS DUAL RANK 8Gbit

Symbol	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866	Unit
IDD0				702	720	mA

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IDD1				801	828	mA
IDD2P-S				198	198	mA
IDD2P-F				252	288	mA
IDD2Q				612	648	mA
IDD2N				648	684	mA
IDD3P				648	684	mA
IDD3N				918	954	mA
IDD4R				1224	1314	mA
IDD4W				1224	1314	mA
IDD5B				2304	2349	mA
IDD6				432	432	mA
IDD6ET				612	612	mA
IDD7				1809	1899	mA

AC CHARACTERISTICS

Refresh parameters by device density

Parameter	Symbol	1Gb	2Gb	4Gb	8Gb	Units	Notes	
REF command to ACT or REF command time	tRFC	110	160	260	350	ns		
Average periodic refresh interval	tREFI	0 °C ≤ TCASE ≤ 85 °C	7.8	7.8	7.8	7.8	µs	
		85 °C < TCASE ≤ 95 °C	3.9	3.9	3.9	3.9	µs	1

Note: 1) Users should refer to the DRAM supplier data sheet and/or the DIMM SPD to determine if DDR3 SDRAM devices support the following options or requirements referred to in this material.

DDR3-800 Speed Bins and Operating Conditions

Speed Bin		DDR3-800		Unit	Notes	
CL-nRCD-nRP		6-6-6				
Parameter	Symbol	min	max			
Internal read command to first data	tAA	15	20	ns		
ACT to internal read or write delay time	tRCD	15	—	ns		
PRE command period	tRP	15	—	ns		
ACT to ACT or REF command period	tRC	52.5	—	ns		
ACT to PRE command period	tRAS	37.5	9 * tREFI	ns		
CL = 6	CWL = 5	tCK(AVG)	2.5	3.3	ns	1, 2, 3
Supported CL Settings		6		nCK	13	
Supported CWL Settings		5		nCK		

DDR3-1066 Speed Bins and Operating Conditions

Speed Bin		DDR3-1066		Unit	Note
CL-nRCD-nRP		7-7-7			
Parameter	Symbol	min	max		
Internal read command to first data	tAA	13.125	20	ns	

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ACT to internal read or write delay time		<i>tRCD</i>	13.125	—	ns	
PRE command period		<i>tRP</i>	13.125	—	ns	
ACT to ACT or REF command period		<i>tRC</i>	50.625	—	ns	
ACT to PRE command period		<i>tRAS</i>	37.5	9 * tREFI	ns	
CL = 6	CWL = 5	<i>tCK(AVG)</i>	2.5	3.3	ns	1,2,3,6,
	CWL = 6	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4,
CL = 7	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4,
	CWL = 6	<i>tCK(AVG)</i>	1.875	< 2.5	ns	1,2,3,4,
CL = 8	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4,
	CWL = 6	<i>tCK(AVG)</i>	1.875	< 2.5	ns	1,2,3,
Supported CL Settings			6, 7, 8		<i>nCK</i>	13
Supported CWL Settings			5, 6		<i>nCK</i>	

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DDR3-1333 Speed Bins and Operating Conditions

Speed Bin		DDR3-1333		Unit	Note	
CL-nRCD-nRP		9-9-9				
Parameter	Symbol	min	max			
Internal read command to first data	<i>tAA</i>	13.5 (13.125)5,11	20	ns		
ACT to internal read or write delay time	<i>tRCD</i>	13.5 (13.125)5,11	—	ns		
PRE command period	<i>tRP</i>	13.5 (13.125)5,11	—	ns		
ACT to ACT or REF command period	<i>tRC</i>	49.5 (49.125)5,11	—	ns		
ACT to PRE command period	<i>tRAS</i>	36	9 * tREFI	ns		
CL = 6	CWL = 5	<i>tCK(AVG)</i>	2.5	3.3	ns	1,2,3,7
	CWL = 6	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4,7
	CWL = 7	<i>tCK(AVG)</i>	Reserved		ns	4
CL = 7	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 6	<i>tCK(AVG)</i>	1.875	< 2.5	ns	1,2,3,4,7
			(Optional)5,11			
CWL = 7	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4	
CL = 8	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 6	<i>tCK(AVG)</i>	1.875	< 2.5	ns	1,2,3,7
	CWL = 7	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4
CL = 9	CWL = 5, 6	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 7	<i>tCK(AVG)</i>	1.5	<1.875	ns	1,2,3,4
CL = 10	CWL = 5, 6	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 7	<i>tCK(AVG)</i>	1.5	<1.875	ns	1,2,3
			(Optional)			
Supported CL Settings		6, 8, (7), 9, (10)		<i>nCK</i>		
Supported CWL Settings		5, 6, 7		<i>nCK</i>		

DDR3-1600 Speed Bins and Operating Conditions

Speed Bin		DDR3-1600		Unit	Note	
CL-nRCD-nRP		11-11-11				
Parameter	Symbol	min	max			
Internal read command to first data	<i>tAA</i>	13.75 (13.125)9	20	ns		
ACT to internal read or write delay time	<i>tRCD</i>	13.75 (13.125)9	—	ns		
PRE command period	<i>tRP</i>	13.75 (13.125)9	—	ns		
ACT to ACT or REF command period	<i>tRC</i>	48.75 (48.125)9	—	ns		
ACT to PRE command period	<i>tRAS</i>	35	9 * tREFI	ns		
CL = 6	CWL = 5	<i>tCK(AVG)</i>	2.5	3.3	ns	1,2,3,7
	CWL = 6	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4,7
	CWL = 7	<i>tCK(AVG)</i>	Reserved		ns	4
CL = 7	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 6	<i>tCK(AVG)</i>	1.875	< 2.5	ns	1,2,3,4,7
			(Optional)5,11			
CWL = 7	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4	
CL = 8	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 6	<i>tCK(AVG)</i>	1.875	< 2.5	ns	1,2,3,7

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Speed Bin		DDR3-1600		Unit	Note	
CL-nRCD-nRP		11-11-11				
Parameter	Symbol	min	max			
CL = 9	CWL = 7	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4
	CWL = 5, 6	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 7	<i>tCK(AVG)</i>	1.5	<1.875	ns	1,2,3,4
CL = 10	CWL = 5, 6	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 7	<i>tCK(AVG)</i>	1.5	<1.875	ns	1,2,3
CL = 11	CWL = 5, 6, 7	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 8	<i>tCK(AVG)</i>	1.25	<1.5	ns	1,2,3,9
Supported CL Settings		6, 8, 7, 9, 10, 11		<i>nCK</i>		
Supported CWL Settings		5, 6, 7, 8		<i>nCK</i>		

DDR3-1866 Speed Bins and Operating Conditions

Speed Bin		DDR3-1866		Unit	Note	
CL-nRCD-nRP		13-13-13				
Parameter	Symbol	min	max			
Internal read command to first data	<i>tAA</i>	13.91 (13.125)10	20	ns		
ACT to internal read or write delay time	<i>tRCD</i>	13.91 (13.125)10	—	ns		
PRE command period	<i>tRP</i>	13.91 (13.125)10	—	ns		
ACT to ACT or REF command period	<i>tRC</i>	47.91 (47.125)10	—	ns		
ACT to PRE command period	<i>tRAS</i>	34	9 * <i>tREFI</i>	ns		
CL = 6	CWL = 5	<i>tCK(AVG)</i>	2.5	3.3	ns	1,2,3,8
	CWL = 6	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4,8
	CWL = 7,8,9	<i>tCK(AVG)</i>	Reserved		ns	4
CL = 7	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 6	<i>tCK(AVG)</i>	1.875	2.5	ns	1,2,3,4,8
	CWL = 7,8,9	<i>tCK(AVG)</i>	Reserved		ns	4
CL = 8	CWL = 5	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 6	<i>tCK(AVG)</i>	1.875	< 2.5	ns	1,2,3,8
	CWL = 7	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4,8
	CWL = 8,9	<i>tCK(AVG)</i>	Reserved			4
CL = 9	CWL = 5, 6	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 7	<i>tCK(AVG)</i>	1.5	1.875	ns	1,2,3,4,8
	CWL = 8	<i>tCK(AVG)</i>	Reserved		ns	4
CL = 10	CWL = 9	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 5, 6	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 7	<i>tCK(AVG)</i>	1.5	<1.875	ns	1,2,3,8
CL = 11	CWL = 8	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4,8
	CWL = 5, 6, 7	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 8	<i>tCK(AVG)</i>	1.25	1.5	ns	1,2,3,9
CL = 12	CWL = 9	<i>tCK(AVG)</i>	Reserved		ns	4
	CWL = 5, 6,7,8	<i>tCK(AVG)</i>	Reserved		ns	1,2,3,4

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Speed Bin		DDR3-1866		Unit	Note	
CL-nRCD-nRP		13-13-13				
Parameter		Symbol	min	max		
CL = 13	CWL = 5, 6,7,8	tCK(AVG)	Reserved		ns	4
	CWL = 9	tCK(AVG)	1.071	<1.25	ns	1,2,3,9
Supported CL Settings		6, 7, 8, 9, 10, 11,13		nCK		
Supported CWL Settings		5, 6, 7, 8,9		nCK		

Speed Bin Table Notes

1. Absolute Specification (TOPER; VDDQ = VDD = 1.35V +/- 0.075 V);
2. The CL setting and CWL setting result in tCK(AVG).MIN and tCK(AVG).MAX requirements. When making a selection of tCK(AVG), both need to be fulfilled: Requirements from CL setting as well as requirements from CWL setting.
3. tCK(AVG).MIN limits: Since CAS Latency is not purely analog - data and strobe output are synchronized by the DLL - all possible intermediate frequencies may not be guaranteed. An application should use the next smaller JEDEC standard tCK(AVG) value (3.0, 2.5, 1.875, 1.5, 1.25, 1.07, or 0.935 ns) when calculating CL [nCK] = tAA [ns] / tCK(AVG) [ns], rounding up to the next 'Supported CL', where tCK(AVG) = 3.0 ns should only be used for CL = 5 calculation.
4. tCK(AVG).MAX limits: Calculate tCK(AVG) = tAA.MAX / CL SELECTED and round the resulting tCK(AVG) down to the next valid speed bin (i.e. 3.3ns or 2.5ns or 1.875 ns or 1.5 ns or 1.25 ns or 1.07 ns or 0.935 ns). This result is tCK(AVG).MAX corresponding to CL SELECTED.
5. 'Reserved' settings are not allowed. User must program a different value.
6. 'Optional' settings allow certain devices in the industry to support this setting; however, it is not a mandatory feature. Refer to supplier's data sheet and/or the DIMM SPD information if and how this setting is supported.
7. Any DDR3-1066 speed bin also supports functional operation at lower frequencies as shown in the table which are not subject to Production Tests but verified by Design/Characterization.
8. Any DDR3-1333 speed bin also supports functional operation at lower frequencies as shown in the table which are not subject to Production Tests but verified by Design/Characterization.
9. Any DDR3-1600 speed bin also supports functional operation at lower frequencies as shown in the table which are not subject to Production Tests but verified by Design/Characterization.
10. For devices supporting optional down binning to CL=7 and CL=9, tAA/tRCD/tRPmin must be 13.125 ns or lower. SPD settings must be programmed to match. For example, DDR3-1333H devices supporting down binning to DDR3-1066F should program 13.125 ns in SPD bytes for tAAmin (Byte 16), tRCDmin (Byte 18), and tRPmin (Byte 20). DDR3-1600K devices supporting down binning to DDR3-1333H or DDR3-1066F should program 13.125 ns in SPD bytes for tAAmin (Byte16), tRCDmin (Byte 18), and tRPmin (Byte 20). Once tRP (Byte 20) is programmed to 13.125ns, tRCmin (Byte 21, 23) also should be programmed accordingly. For example, 49.125ns (tRASmin + tRPmin = 36 ns + 13.125 ns) for DDR3-1333H and 48.125ns (tRASmin + tRPmin = 35 ns + 13.125 ns) for DDR3-1600K.

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Timing Parameters

Parameter	Symbol	DDR3-800		DDR3-1066		DDR3-1333		Units	Note
		MIN	MAX	MIN	MAX	MIN	MAX		
Clock Timing									
Minimum Clock Cycle Time (DLL off mode)	tCK(DLL_OF F)	8	-	8	-	8	-	ns	6
Average Clock Period	tCK(avg)	See Speed Bins Table						ps	
Clock Period	tCK(abs)	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	ps	
Average high pulse width	tCH(avg)	0.47	0.53	0.47	0.53	0.47	0.53	tCK(avg)	
Average low pulse width	tCL(avg)	0.47	0.53	0.47	0.53	0.47	0.53	tCK(avg)	
Clock Period Jitter	tJIT(per)	-100	100	-90	90	-80	80	ps	
Clock Period Jitter during DLL locking period	tJIT(per, lck)	-90	90	-80	80	-70	70	ps	
Cycle to Cycle Period Jitter	tJIT(cc)	200		180		160		ps	
Cycle to Cycle Period Jitter during DLL locking period	tJIT(cc, lck)	180		160		140		ps	
Cumulative error across 2 cycles	tERR(2per)	- 147	147	- 132	132	- 118	118	ps	
Cumulative error across 3 cycles	tERR(3per)	- 175	175	- 157	157	- 140	140	ps	
Cumulative error across 4 cycles	tERR(4per)	- 194	194	- 175	175	- 155	155	ps	
Cumulative error across 5 cycles	tERR(5per)	- 209	209	- 188	188	- 168	168	ps	
Cumulative error across 6 cycles	tERR(6per)	- 222	222	- 200	200	- 177	177	ps	
Cumulative error across 7 cycles	tERR(7per)	- 232	232	- 209	209	- 186	186	ps	
Cumulative error across 8 cycles	tERR(8per)	- 241	241	- 217	217	- 193	193	ps	
Cumulative error across 9 cycles	tERR(9per)	- 249	249	- 224	224	- 200	200	ps	
Cumulative error across 10 cycles	tERR(10per)	- 257	257	- 231	231	- 205	205	ps	
Cumulative error across 11 cycles	tERR(11per)	- 263	263	- 237	237	- 210	210	ps	
Cumulative error across 12 cycles	tERR(12per)	- 269	269	- 242	242	- 215	215	ps	
Cumulative error across n = 13, 14 ... 49, 50 cycles	tERR(nper)	tERR(nper)min = (1 + 0.68ln(n))*tJIT(per)min tERR(nper)max = (1 + 0.68ln(n))*tJIT(per)max						ps	24
Absolute clock HIGH pulse width	tCH(abs)	0.43	-	0.43	-	0.43	-	tCK(avg)	25
Absolute clock Low pulse width	tCL(abs)	0.43	-	0.43	-	0.43	-	tCK(avg)	26
Data Timing									
DQS, DQS to DQ skew, per group, per access	tDQSQ	-	200	-	150	-	125	ps	13
DQ output hold time from DQS, DQS	tQH	0.38	-	0.38	-	0.38	-	tCK(avg)	13, g
DQ low-impedance time from CK, CK	tLZ(DQ)	-800	400	-600	300	-500	250	ps	13,14, f
DQ high-impedance time from CK, CK	tHZ(DQ)	-	400	-	300	-	250	ps	13,14, f
Data setup time to DQS, DQS referenced to VIH(AC)VIL(AC) levels	tDS(base)	75	-	25	-	30	-	ps	d, 17
Data hold time to DQS, DQS referenced to VIH(AC)VIL(AC) levels	tDH(base)	150	-	100	-	65	-	ps	d, 17
DQ and DM Input pulse width for each input	tDIPW	600	-	490	-	400	-	ps	28
Data Strobe Timing									
DQS, DQS READ Preamble	tRPRE	0.9	Note 19	0.9	Note 19	0.9	Note 19	tCK	13, 19, g
DQS, DQS differential READ Postamble	tRPST	0.3	Note 11	0.3	Note 11	0.3	Note 11	tCK	11, 13, b
DQS, DQS output high time	tQSH	0.38	-	0.38	-	0.4	-	tCK(avg)	13, g
DQS, DQS output low time	tQSL	0.38	-	0.38	-	0.4	-	tCK(avg)	13, g
DQS, DQS WRITE Preamble	tWPRE	0.9	-	0.9	-	0.9	-	tCK	
DQS, DQS WRITE Postamble	tWPST	0.3	-	0.3	-	0.3	-	tCK	
DQS, DQS rising edge output access time from rising CK, CK	tDQSCK	-400	400	-300	300	-255	255	ps	13, f
DQS, DQS low-impedance time (Referenced from RL-1)	tLZ(DQS)	-800	400	-600	300	-500	250	ps	13,14, f
DQS, DQS high-impedance time (Referenced from RL+BL/2)	tHZ(DQS)	-	400	-	300	-	250	ps	12,13,14
DQS, DQS differential input low pulse width	tDQSL	0.45	0.55	0.45	0.55	0.45	0.55	tCK	29, 31
DQS, DQS differential input high pulse width	tDQSH	0.45	0.55	0.45	0.55	0.45	0.55	tCK	30, 31
DQS, DQS rising edge to CK, CK rising edge	tDQSS	-0.25	0.25	-0.25	0.25	-0.25	0.25	tCK(avg)	c
DQS, DQS falling edge setup time to CK, CK rising edge	tDSS	0.2	-	0.2	-	0.2	-	tCK(avg)	c, 32
DQS, DQS falling edge hold time to CK, CK rising edge	tDSH	0.2	-	0.2	-	0.2	-	tCK(avg)	c, 32

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Timing Parameters (Cont.)

Speed	Parameter	Symbol	DDR3-800		DDR3-1066		DDR3-1333		Units	Note	
			MIN	MAX	MIN	MAX	MIN	MAX			
Command and Address Timing											
	DLL locking time	tDLLK	512	-	512	-	512	-	nCK		
	internal READ Command to PRECHARGE Command delay	tRTP	max (4nCK,7.5ns)	-	max (4nCK,7.5ns)	-	max (4nCK,7.5ns)	-		e	
	Delay from start of internal write transaction to internal read command	tWTR	max (4nCK,7.5ns)	-	max (4nCK,7.5ns)	-	max (4nCK,7.5ns)	-		e,18	
	WRITE recovery time	tWR	15	-	15	-	15	-	ns	e	
	Mode Register Set command cycle time	tMRD	4	-	4	-	4	-	nCK		
	Mode Register Set command update delay	tMOD	max (12nCK,15ns)	-	max (12nCK,15ns)	-	max (12nCK,15ns)	-			
	CAS# to CAS# command delay	tCCD	4	-	4	-	4	-	nCK		
	Auto precharge write recovery + precharge time	tDAL(min)	WR + roundup (tRP / tCK(AVG))							nCK	
	Multi-Purpose Register Recovery Time	tMPRR	1	-	1	-	1	-	nCK	22	
	ACTIVE to PRECHARGE command period	tRAS	See 13.3 " Speed Bins and CL, tRCD, tRP, tRC and tRAS for corresponding Bin" on page 37							ns	e
	ACTIVE to ACTIVE command period for 1KB page size	tRRD	max (4nCK,10ns)	-	max (4nCK,7.5ns)	-	max (4nCK,6ns)	-		e	
	ACTIVE to ACTIVE command period for 2KB page size	tRRD	max (4nCK,10ns)	-	max (4nCK,10ns)	-	max (4nCK,7.5ns)	-		e	
	Four activate window for 1KB page size	tFAW	40	-	37.5	-	30	-	ns	e	
	Four activate window for 2KB page size	tFAW	50	-	50	-	45	-	ns	e	
	Command and Address setup time to CK, CK referenced to VIH(AC) / VIL(AC) levels	tIS(base)	200	-	125	-	65	-	ps	b,16	
	Command and Address hold time from CK, CK referenced to VIH(AC) / VIL(AC) levels	tIH(base)	275	-	200	-	140	-	ps	b,16	
	Command and Address setup time to CK, CK referenced to VIH(AC) / VIL(AC) levels	tIS(base) AC150	200 + 150	-	125 + 150	-	65+125	-	ps	b,16,27	
	Control & Address Input pulse width for each input	tIPW	900	-	780	-	620	-	ps	28	
Calibration Timing											
	Power-up and RESET calibration time	tZQinit	512	-	512	-	512	-	nCK		
	Normal operation Full calibration time	tZQoper	256	-	256	-	256	-	nCK		
	Normal operation short calibration time	tZQCS	64	-	64	-	64	-	nCK	23	
Reset Timing											
	Exit Reset from CKE HIGH to a valid command	tXPR	max(5nCK, tRFC + 10ns)	-	max(5nCK, tRFC + 10ns)	-	max(5nCK, tRFC + 10ns)	-			
Self Refresh Timing											
	Exit Self Refresh to commands not requiring a locked DLL	tXS	max(5nCK,tRFC + 10ns)	-	max(5nCK,tRFC + 10ns)	-	max(5nCK,tRFC + 10ns)	-			
	Exit Self Refresh to commands requiring a locked DLL	tXSDLL	tDLLK(min)	-	tDLLK(min)	-	tDLLK(min)	-	nCK		
	Minimum CKE low width for Self refresh entry to exit timing	tCKESR	tCKE(min) + 1tCK	-	tCKE(min) + 1tCK	-	tCKE(min) + 1tCK	-			
	Valid Clock Requirement after Self Refresh Entry (SRE) or Power-Down Entry (PDE)	tCKSRE	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-			
	Valid Clock Requirement before Self Refresh Exit (SRX) or Power-Down Exit (PDX) or Reset Exit	tCKSRX	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-			

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Timing Parameters(Cont.)

Speed		DDR3-800		DDR3-1066		DDR3-1333		Units	Note
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX		
Power Down Timing									
Exit Power Down with DLL on to any valid command;Exit Precharge Power Down with DLL frozen to commands not requiring a locked DLL	tXP	max (3nCK, 7.5ns)	-	max (3nCK, 7.5ns)	-	max (3nCK,6ns)	-		
Exit Precharge Power Down with DLL frozen to commands requiring a locked DLL	tXPDLL	max (10nCK, 24ns)	-	max (10nCK, 24ns)	-	max (10nCK, 24ns)	-		2
CKE minimum pulse width	tCKE	max (3nCK, 7.5ns)	-	max (3nCK, 5.625ns)	-	max (3nCK, 5.625ns)	-		
Command pass disable delay	tCPDED	1	-	1	-	1	-	nCK	
Power Down Entry to Exit Timing	tPD	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI	tCK	15
Timing of ACT command to Power Down entry	tACTPDEN	1	-	1	-	1	-	nCK	20
Timing of PRE command to Power Down entry	tPRPDEN	1	-	1	-	1	-	nCK	20
Timing of RD/RDA command to Power Down entry	tRDPDEN	RL + 4 + 1	-	RL + 4 + 1	-	RL + 4 + 1	-		
Timing of WR command to Power Down entry (BL8OTF, BL8MRS, BL4OTF)	tWRPDEN	WL + 4 +(tWR/ tCK(avg))	-	WL + 4 +(tWR/ tCK(avg))	-	WL + 4 +(tWR/ tCK(avg))	-	nCK	9
Timing of WRA command to Power Down entry (BL8OTF, BL8MRS, BL4OTF)	tWRAPDEN	WL + 4 +WR + 1	-	WL + 4 +WR + 1	-	WL + 4 +WR + 1	-	nCK	10
Timing of WR command to Power Down entry (BL4MRS)	tWRPDEN	WL + 2 +(tWR/ tCK(avg))	-	WL + 2 +(tWR/ tCK(avg))	-	WL + 2 +(tWR/ tCK(avg))	-	nCK	9
Timing of WRA command to Power Down entry (BL4MRS)	tWRAPDEN	WL + 2 +WR + 1	-	WL + 2 +WR + 1	-	WL + 2 +WR + 1	-	nCK	10
Timing of REF command to Power Down entry	tREFPDEN	1	-	1	-	1	-		20,21
Timing of MRS command to Power Down entry	tMRSPDEN	tMOD(min)	-	tMOD(min)	-	tMOD(min)	-		
ODT Timing									
ODT high time without write command or with write command and BC4	ODTH4	4	-	4	-	4	-	nCK	
ODT high time with Write command and BL8	ODTH8	6	-	6	-	6	-	nCK	
Asynchronous RTT turn-on delay (Power-Down with DLL frozen)	tAONPD	2	8.5	2	8.5	2	8.5	ns	
Asynchronous RTT turn-off delay (Power-Down with DLL frozen)	tAOFPD	2	8.5	2	8.5	2	8.5	ns	
ODT turn-on	tAON	-400	400	-300	300	-250	250	ps	7,f
RTT_NOM and RTT_WR turn-off time from ODTLoff reference	tAOF	0.3	0.7	0.3	0.7	0.3	0.7	tCK(avg)	8,f
RTT dynamic change skew	tADC	0.3	0.7	0.3	0.7	0.3	0.7	tCK(avg)	f
Write Leveling Timing									
First DQS pulse rising edge after tDQSS margining mode is programmed	tWLMRD	40	-	40	-	40	-	tCK	3
DQS/DQS delay after tDQS margining mode is programmed	tWLDQSEN	25	-	25	-	25	-	tCK	3
Setup time for tDQSS latch	tWLS	325	-	245	-	195	-	ps	
Write leveling hold time from rising DQS, DQS crossing to rising CK, CK crossing	tWLH	325	-	245	-	195	-	ps	
Write leveling output delay	tWLO	0	9	0	9	0	9	ns	
Write leveling output error	tWLOE	0	2	0	2	0	2	ns	

Timing Parameters (Cont.)

Speed		DDR3-1600		DDR3-1866		Units	Note
Parameter	Symbol	MIN	MAX	MIN	MAX		
Clock Timing							
Minimum Clock Cycle Time (DLL off mode)	tCK(DLL OFF F)	8	-	8	-	ns	6
Average Clock Period	tCK(avg)	See Speed Bins Table				ps	
Clock Period	tCK(abs)	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	tCK(avg)min + tJIT(per)min	tCK(avg)max + tJIT(per)max	ps	
Average high pulse width	tCH(avg)	0.47	0.53	0.47	0.53	tCK(avg)	

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Speed	Parameter		DDR3-1600		DDR3-1866		Units		Note	
	Symbol	MIN	MAX	MIN	MAX	MIN	MAX			
Clock Timing										
Average low pulse width	tCL(avg)	0.47	0.53	0.47	0.53			tCK(avg)		
Clock Period Jitter	tJIT(per)	-70	70	-60	60			ps		
Clock Period Jitter during DLL locking period	tJIT(per, lck)	-60	60	-50	50			ps		
Cycle to Cycle Period Jitter	tJIT(cc)	140		120				ps		
Cycle to Cycle Period Jitter during DLL locking period	tJIT(cc, lck)	120		100				ps		
Cumulative error across 2 cycles	tERR(2per)	- 103	103	- 88	88			ps		
Cumulative error across 3 cycles	tERR(3per)	- 122	122	- 105	105			ps		
Cumulative error across 4 cycles	tERR(4per)	- 136	136	- 117	117			ps		
Cumulative error across 5 cycles	tERR(5per)	- 147	147	- 126	126			ps		
Cumulative error across 6 cycles	tERR(6per)	- 155	155	- 133	133			ps		
Cumulative error across 7 cycles	tERR(7per)	- 163	163	- 139	139			ps		
Cumulative error across 8 cycles	tERR(8per)	- 169	169	- 145	145			ps		
Cumulative error across 9 cycles	tERR(9per)	- 175	175	- 150	150			ps		
Cumulative error across 10 cycles	tERR(10per)	- 180	180	- 154	154			ps		
Cumulative error across 11 cycles	tERR(11per)	- 184	184	- 158	158			ps		
Cumulative error across 12 cycles	tERR(12per)	- 188	188	- 161	161			ps		
Cumulative error across n = 13, 14 ... 49, 50 cycles	tERR(nper)	tERR(nper)min = (1 + 0.68ln(n))*tJIT(per)min tERR(nper)max = (1 + 0.68ln(n))*tJIT(per)max							ps	24
Absolute clock HIGH pulse width	tCH(abs)	0.43	-	0.43	-			tCK(avg)	25	
Absolute clock Low pulse width	tCL(abs)	0.43	-	0.43	-			tCK(avg)	26	
Data Timing										
DQS, DQS to DQ skew, per group, per access	tDQSQ	-	100	-	85			ps	13	
DQ output hold time from DQS, DQS	tQH	0.38	-	0.38	-			tCK(avg)	13, g	
DQ low-impedance time from CK, CK	tLZ(DQ)	-450	225	-390	195			ps	13,14, f	
DQ high-impedance time from CK, CK	tHZ(DQ)	-	225	-	195			ps	13,14, f	
Data setup time to DQS, DQS referenced to VIH(AC)VIL(AC) levels	tDS(base)	10	-	-	-			ps	d, 17	
Data hold time to DQS, DQS referenced to VIH(AC)VIL(AC) levels	tDH(base)	-	-	0	-			ps	d, 17	
DQ and DM Input pulse width for each input	tDIPW	360	-	320	-			ps	28	
Data Strobe Timing										
DQS, DQS READ Preamble	tRPRE	0.9	Note 19	0.9	Note 19			tCK	13, 19, g	
DQS, DQS differential READ Postamble	tRPST	0.3	Note 11	0.3	Note 11			tCK	11, 13, b	
DQS, DQS output high time	tQSH	0.4	-	0.4	-			tCK(avg)	13, g	
DQS, DQS output low time	tQSL	0.4	-	0.4	-			tCK(avg)	13, g	
DQS, DQS WRITE Preamble	tWPRE	0.9	-	0.9	-			tCK		
DQS, DQS WRITE Postamble	tWPST	0.3	-	0.3	-			tCK		
DQS, DQS rising edge output access time from rising CK, CK	tDQSCCK	-225	225	-195	195			ps	13, f	
DQS, DQS low-impedance time (Referenced from RL-1)	tLZ(DQS)	-450	225	-390	195			ps	13,14, f	
DQS, DQS high-impedance time (Referenced from RL+BL/2)	tHZ(DQS)	-	225	-	195			ps	12,13,14	
DQS, DQS differential input low pulse width	tDQSL	0.45	0.55	0.45	0.55			tCK	29, 31	
DQS, DQS differential input high pulse width	tDQSH	0.45	0.55	0.45	0.55			tCK	30, 31	
DQS, DQS rising edge to CK, CK rising edge	tDQSS	-0.27	0.27	-0.27	0.27			tCK(avg)	c	
DQS, DQS falling edge setup time to CK, CK rising edge	tDSS	0.9	Note 19	0.18	-			tCK(avg)	c, 32	
DQS, DQS falling edge hold time to CK, CK rising edge	tDSH	0.3	Note 11	0.18	-			tCK(avg)	c, 32	

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Timing Parameters (Cont.)

Speed		DDR3-1600		DDR3-1866				Units	Note	
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX			
Command and Address Timing										
DLL locking time	tDLLK	512	-	512	-			nCK		
internal READ Command to PRECHARGE Command delay	tRTP	max (4nCK,7.5ns)	-	max (4nCK,7.5ns)	-				e	
Delay from start of internal write transaction to internal read command	tWTR	max (4nCK,7.5ns)	-	max (4nCK,7.5ns)	-				e,18	
WRITE recovery time	tWR	15	-	15	-			ns	e	
Mode Register Set command cycle time	tMRD	4	-	4	-			nCK		
Mode Register Set command update delay	tMOD	max (12nCK,15ns)	-	max (12nCK,15ns)	-					
CAS# to CAS# command delay	tCCD	4	-	4	-			nCK		
Auto precharge write recovery + precharge time	tDAL(min)	WR + roundup (tRP / tCK(AVG))							nCK	
Multi-Purpose Register Recovery Time	tMPRR	1	-	1	-			nCK	22	
ACTIVE to PRECHARGE command period	tRAS	See " Speed Bins and CL, tRCD, tRP, tRC and tRAS for corresponding Bin"							ns	e
ACTIVE to ACTIVE command period for 1KB page size	tRRD	max (4nCK,6ns)	-	max (4nCK,5ns)	-				e	
ACTIVE to ACTIVE command period for 2KB page size	tRRD	max (4nCK,7.5ns)	-	max (4nCK,6ns)	-				e	
Four activate window for 1KB page size	tFAW	30	-	27	-			ns	e	
Four activate window for 2KB page size	tFAW	40	-	35	-			ns	e	
Command and Address setup time to CK, CK referenced to VIH(AC) / VIL(AC) levels	tIS(base)	170	-	-	-			ps	b,16	
Command and Address hold time from CK, CK referenced to VIH(AC) / VIL(AC) levels	tIH(base)	120	-	100	-			ps	b,16	
Command and Address setup time to CK, CK referenced to VIH(AC) / VIL(AC) levels	tIS(base) AC150	-	-	-	-			ps	b,16,27	
Control & Address Input pulse width for each input	tIPW	560	-	535	-			ps	28	
Calibration Timing										
Power-up and RESET calibration time	tZQinit	512	-	Max(512nCK,640ns)	-			nCK		
Normal operation Full calibration time	tZQoper	256	-	Max(256nCK,320ns)	-			nCK		
Normal operation short calibration time	tZQCS	64	-	Max(64nCK,80ns)	-			nCK	23	
Reset Timing										
Exit Reset from CKE HIGH to a valid command	tXPR	max(5nCK, tRFC + 10ns)	-	max(5nCK, tRFC + 10ns)	-	max(5nCK, tRFC + 10ns)	-			
Self Refresh Timing										
Exit Self Refresh to commands not requiring a locked DLL	tXS	max(5nCK, tRFC + 10ns)	-	max(5nCK, tRFC + 10ns)	-	max(5nCK, tRFC + 10ns)	-			
Exit Self Refresh to commands requiring a locked DLL	tXSDLL	tDLLK(min)	-	tDLLK(min)	-	tDLLK(min)	-	nCK		
Minimum CKE low width for Self refresh entry to exit timing	tCKESR	tCKE(min) + 1tCK	-	tCKE(min) + 1tCK	-	tCKE(min) + 1tCK	-			
Valid Clock Requirement after Self Refresh Entry (SRE) or Power-Down Entry (PDE)	tCKSRE	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-			
Valid Clock Requirement before Self Refresh Exit (SRX) or Power-Down Exit (PDX) or Reset Exit	tCKSRX	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-	max(5nCK, 10ns)	-			

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Timing Parameters(Cont.)

Speed		DDR3-1600		DDR3-1866				Units	Note
Parameter	Symbol	MIN	MAX	MIN	MAX	MIN	MAX		
Power Down Timing									
Exit Power Down with DLL on to any valid command;Exit Precharge Power Down with DLL frozen to commands not requiring a locked DLL	tXP	max (3nCK, 6ns)	-	max (3nCK, 6ns)	-				
Exit Precharge Power Down with DLL frozen to commands requiring a locked DLL	tXPDLL	max (10nCK, 24ns)	-	max (10nCK, 24ns)	-				2
CKE minimum pulse width	tCKE	max (3nCK, 5ns)	-	max (3nCK, 5ns)	-				
Command pass disable delay	tCPDED	1	-	1	-			nCK	
Power Down Entry to Exit Timing	tPD	tCKE(min)	9*tREFI	tCKE(min)	9*tREFI			tCK	15
Timing of ACT command to Power Down entry	tACTPDEN	1	-	1	-			nCK	20
Timing of PRE command to Power Down entry	tPRPDEN	1	-	1	-			nCK	20
Timing of RD/RDA command to Power Down entry	tRDPDEN	RL + 4 + 1	-	RL + 4 + 1	-				
Timing of WR command to Power Down entry (BL8OTF, BL8MRS, BL4OTF)	tWRPDEN	WL + 4 +(tWR/tCK(avg))	-	WL + 4 +(tWR/tCK(avg))	-			nCK	9
Timing of WRA command to Power Down entry (BL8OTF, BL8MRS, BL4OTF)	tWRAPDEN	WL + 4 +WR + 1	-	WL + 4 +WR + 1	-			nCK	10
Timing of WR command to Power Down entry (BL4MRS)	tWRPDEN	WL + 2 +(tWR/tCK(avg))	-	WL + 2 +(tWR/tCK(avg))	-			nCK	9
Timing of WRA command to Power Down entry (BL4MRS)	tWRAPDEN	WL + 2 +WR + 1	-	WL + 2 +WR + 1	-			nCK	10
Timing of REF command to Power Down entry	tREFPDEN	1	-	1	-				20,21
Timing of MRS command to Power Down entry	tMRSPDEN	tMOD(min)	-	tMOD(min)	-				
ODT Timing									
ODT high time without write command or with write command and BC4	ODTH4	4	-	4	-			nCK	
ODT high time with Write command and BL8	ODTH8	6	-	6	-			nCK	
Asynchronous RTT turn-on delay (Power-Down with DLL frozen)	tAONPD	2	8.5	2	8.5			ns	
Asynchronous RTT turn-off delay (Power-Down with DLL frozen)	tAOFPD	2	8.5	2	8.5			ns	
ODT turn-on	tAON	-225	225	-195	195			ps	7,f
RTT_NOM and RTT_WR turn-off time from ODTLoff reference	tAOF	0.3	0.7	0.3	0.7			tCK(avg)	8,f
RTT dynamic change skew	tADC	0.3	0.7	0.3	0.7			tCK(avg)	f
Write Leveling Timing									
First DQS pulse rising edge after tDQSS margining mode is programmed	tWLMRD	40	-	40	-			tCK	3
DQS/DQS delay after tDQSS margining mode is programmed	tWLDQSEN	25	-	25	-			tCK	3
Setup time for tDQSS latch	tWLS	165	-	140	-			ps	
Write leveling hold time from rising DQS, DQS crossing to rising CK, CK crossing	tWLH	165	-	140	-			ps	
Write leveling output delay	tWLO	0	7.5	0	7.5			ns	
Write leveling output error	tWLOE	0	2	0	2			ns	

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18.1 Jitter Notes

1. Unit 'tCK(avg)' represents the actual tCK(avg) of the input clock under operation. Unit 'nCK' represents one clock cycle of the input clock, counting the actual clock edges. ex) tMRD = 4 [nCK] means; if one Mode Register Set command is registered at Tm, another Mode Register Set command may be registered at Tm+4, even if (Tm+4 - Tm) is 4 x tCK(avg) + tERR(4per),min.
2. These parameters are measured from a command/address signal (CKE, CS, RAS, CAS, WE, ODT, BA0, A0, A1, etc.) transition edge to its respective clock signal (CK/CK) crossing. The spec values are not affected by the amount of clock jitter applied (i.e. tJIT(per), tJIT(cc), etc.), as the setup and hold are relative to the clock signal crossing that latches the command/address. That is, these parameters should be met whether clock jitter is present or not.
3. These parameters are measured from a data strobe signal (DQS(L/U), DQS(L/U)) crossing to its respective clock signal (CK, CK) crossing. The spec values are not affected by the amount of clock jitter applied (i.e. tJIT(per), tJIT(cc), etc.), as these are relative to the clock signal crossing. That is, these parameters should be met whether clock jitter is present or not.
4. These parameters are measured from a data signal (DM(L/U), DQ(L/U)0, DQ(L/U)1, etc.) transition edge to its respective data strobe signal (DQS(L/U), DQS(L/U)#) crossing. Specific Note e For these parameters, the DDR3 SDRAM device supports tnPARAM [nCK] = RU{ tPARAM [ns] / tCK(avg) [ns] }, which is in clock cycles, assuming all input clock jitter specifications are satisfied. For example, the device will support tnRP = RU{tRP / tCK(avg)}, which is in clock cycles, if all input clock jitter specifications are met. This means: For DDR3-800 6-6-6, of which tRP = 15ns, the device will support tnRP = RU{tRP / tCK(avg)} = 6, as long as the input clock jitter specifications are met, i.e. Precharge command at Tm and Active command at Tm+6 is valid even if (Tm+6 - Tm) is less than 15ns due to input clock jitter.
5. When the device is operated with input clock jitter, this parameter needs to be derated by the actual tERR(mper),act of the input clock, where 2 <= m <= 12. (output deratings are relative to the SDRAM input clock.) For example, if the measured jitter into a DDR3-800 SDRAM has tERR(mper),act,min = - 172 ps and tERR(mper),act,max = + 193 ps, then tDQSCK,min(derated) = tDQSCK,min - tERR(mper),act,max = - 400 ps - 193 ps = - 593 ps and tDQSCK,max(derated) = tDQSCK,max - tERR(mper),act,min = 400 ps + 172 ps = + 572 ps. Similarly, tLZ(DQ) for DDR3-800 derates to tLZ(DQ),min(derated) = 800 ps - 193 ps = - 993 ps and tLZ(DQ),max(derated) = 400 ps + 172 ps = + 572 ps. (Caution on the min/max usage!) Note that tERR(mper),act,min is the minimum measured value of tERR(nper) where 2 <= n <= 12, and tERR(mper),act,max is the maximum measured value of tERR(nper) where 2 <= n <= 12.
6. When the device is operated with input clock jitter, this parameter needs to be derated by the actual tJIT(per),act of the input clock. (output deratings are relative to the SDRAM input clock.) For example, if the measured jitter into a DDR3-800 SDRAM has tCK(avg),act = 2500 ps, tJIT(per),act,min = - 72 ps and tJIT(per),act,max = + 93 ps, then tRPRE,min(derated) = tRPRE,min + tJIT(per),act,min = 0.9 x tCK(avg),act + tJIT(per),act,min = 0.9 x 2500 ps - 72 ps = + 2178 ps. Similarly, tQH,min(derated) = tQH,min + tJIT(per),act,min = 0.38 x tCK(avg),act + tJIT(per),act,min = 0.38 x 2500 ps - 72 ps = + 878 ps. (Caution on the min/max usage!)= 0.38 x 2500 ps - 72 ps = + 878 ps. (Caution on the min/max usage!)

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18.2 Timing Parameter Notes

1. Actual value dependant upon measurement level definitions which are TBD.
2. Commands requiring a locked DLL are: READ (and RAP) and synchronous ODT commands.
3. The max values are system dependent.
4. WR as programmed in mode register
5. Value must be rounded-up to next higher integer value
6. There is no maximum cycle time limit besides the need to satisfy the refresh interval, tREFI.
7. For definition of RTT turn-on time tAON see "Device Operation"
8. For definition of RTT turn-off time tAOF see "Device Operation".
9. tWR is defined in ns, for calculation of tWRPDEN it is necessary to round up tWR / tCK to the next integer.
10. WR in clock cycles as programmed in MR0
11. The maximum read postamble is bound by tDQSCK(min) plus tQSH(min) on the left side and tHZ(DQS)max on the right side. Device Operation.
12. Output timing deratings are relative to the SDRAM input clock. When the device is operated with input clock jitter, this parameter needs to be derated by TBD
13. Value is valid for RON34
14. Single ended signal parameter.
15. tREFI depends on TOPER
16. tIS(base) and tIH(base) values are for 1V/ns CMD/ADD single-ended slew rate and 2V/ns CK, CK differential slew rate, Note for DQ and DM signals, VREF(DC) = VREFDQ(DC). For input only pins except RESET, VREF(DC)=VREFCA(DC). See "Address/ Command Setup, Hold and Derating"
17. tDS(base) and tDH(base) values are for 1V/ns DQ single-ended slew rate and 2V/ns DQS, DQS differential slew rate. Note for DQ and DM signals, VREF(DC)= VREFDQ(DC). For input only pins except RESET, VREF(DC)=VREFCA(DC). See "Data Setup, Hold and Slew Rate Derating"
18. Start of internal write transaction is defined as follows ;
For BL8 (fixed by MRS and on-the-fly) : Rising clock edge 4 clock cycles after WL.
For BC4 (on-the-fly) : Rising clock edge 4 clock cycles after WL
For BC4 (fixed by MRS) : Rising clock edge 2 clock cycles after WL
19. The maximum read preamble is bound by tLZDQS(min) on the left side and tDQSCK(max) on the right side. See "Device Operation"
20. CKE is allowed to be registered low while operations such as row activation, precharge, autoprecharge or refresh are in progress, but power-down IDD spec will not be applied until finishing those operations.
21. Although CKE is allowed to be registered LOW after a REFRESH command once tREFPDEN(min) is satisfied, there are cases where additional time such as tXPDLL(min) is also required. See "Device Operation".
22. Defined between end of MPR read burst and MRS which reloads MPR or disables MPR function.
23. One ZQCS command can effectively correct a minimum of 0.5 % (ZQCorrection) of RON and RTT impedance error within 64 nCK for all speed bins assuming the maximum sensitivities specified in the 'Output Driver Voltage and Temperature Sensitivity' and 'ODT Voltage and Temperature Sensitivity' tables. The appropriate interval between ZQCS commands can be determined from these tables and other application specific parameters. One method for calculating the interval between ZQCS commands, given the temperature (Tdriftrate) and voltage (Vdriftrate) drift rates that the SDRAM is subject to in the application, is illustrated. The interval could be defined by the following formula:

$$\frac{ZQCorrection}{(TSens \times Tdriftrate) + (VSens \times Vdriftrate)}$$

where TSens = max(dRTTdT, dRONdTM) and VSens = max(dRTTdV, dRONdVM) define the SDRAM temperature and voltage sensitivities.

For example, if TSens = 1.5% /°C, VSens = 0.15% / mV, Tdriftrate = 1°C / sec and Vdriftrate = 15 mV / sec, then the interval between ZQCS commands is calculated as:

$$\frac{0.5}{(1.5 \times 1) + (0.15 \times 15)} = 0.133 \sim 128\text{ms}$$

24. n = from 13 cycles to 50 cycles. This row defines 38 parameters.
25. tCH(abs) is the absolute instantaneous clock high pulse width, as measured from one rising edge to the following falling edge.
26. tCL(abs) is the absolute instantaneous clock low pulse width, as measured from one falling edge to the following rising edge.
27. The tIS(base) AC150 specifications are adjusted from the tIS(base) specification by adding an additional 100 ps of derating to accommodate for the lower alternate threshold of 150 mV and another 25 ps to account for the earlier reference point [(175 mv - 150 mV) / 1 V/ns].
28. Pulse width of a input signal is defined as the width between the first crossing of VREF(DC) and the consecutive crossing of VREF(DC)
29. tDQSL describes the instantaneous differential input low pulse width on DQS-DQS, as measured from one falling edge to the next consecutive rising edge.
30. tDQSH describes the instantaneous differential input high pulse width on DQS-DQS, as measured from one rising edge to the next consecutive falling edge.
31. tDQSH, act + tDQSL, act = 1 tCK, act ; with tXYZ, act being the actual measured value of the respective timing parameter in the application.
32. tDSH, act + tDSS, act = 1 tCK, act ; with tXYZ, act being the actual measured value of the respective timing parameter in the application.

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REVISION HISTORY

Revision	Release Date	Description of Change	Checked By (Full Name)
A	August 29, 2012	Created 1.35V based datasheet	
A1	November 28, 2012	Remove unsupported PN's using CL8 and CL10, Add 8GB PN's (1432PCB) . Removed ramstack on mechanical dwg and revised module thickness.	
A2	June 20, 2013	Revised mechanical drawing to show dimension in mm and a nominal thickness with tolerance	
A3	January 2, 2014	Revised the tRFC for 4Gb from 300ns to 260ns	Chanhee Park
B	September 05, 2014	Add features note that module is backward compatible with 1.5V DDR3 DIMMs. Update DC OPERATING CONDITIONS AND CHARACTERISTICS table for 1.5V (A4, August 05, 2014)	
C	September 23, 2014	Add max thickness to mechanical outline	
D	April 27, 2015	Revise IDD values. Remove CL10 PN's Updated the 2rank mechanical drawing. IDC review	
E	July 20, 2017	Revise logo. Change company address	

STATEMENT OF COMPLIANCE

Viking Technology(tm), Sanmina Corporation ("Viking") shall use commercially reasonable efforts to provide components, parts, materials, products and processes to Customer that do not contain: (i) lead, mercury, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE) above 0.1% by weight in homogeneous material or (ii) cadmium above 0.01% by weight of homogeneous material, except as provided in any exemption(s) from RoHS requirements (including the most current version of the "Annex" to Directive 2002/95/EC of 27 January, 2003), as codified in the specific laws of the EU member countries. Viking strives to obtain appropriate contractual protections from its suppliers in connection with the RoHS Directives.

All printed circuit boards (PCBs) have a flammability rating of UL94V-0.

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